

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (mΩ) (TYP.)	I _D (A)	Q _g (TYP.)		
100	1.7 at V _{GS} = 10 V	280	134 nC		

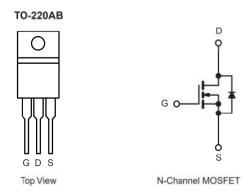
FEATURES

- DT-TrenchPower MOSFET
- \bullet 100 % R_{g} and UIS tested



APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- · Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management



PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	100	V		
Gate-Source Voltage		V _{GS}			± 20
O 11 D 1 O 1/T 15000)	T _C = 25 °C		280	_	
Continuous Drain Current (T _J = 150 °C)	T _C = 100 °C		153		
Pulsed Drain Current (t = 100 μs)	I _{DM}	1120	А		
Avalanche Current	L = 0.1 mH	I _{AS}	155		
Single Avalanche Energy ^a	L = 0.1 IIII	E _{AS}	2388	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	D-	415 ^b	w	
Maximum Fower Dissipation ~	T _C = 100 °C	P _D	166 ^b		
Operating Junction and Storage Temperature F	T _J , T _{stg}	-55 to +150	°C		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	65	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.35	C/VV	

Notes

- a. Duty cycle ≤ 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).



Drain-Source Breakdown Voltage VDS VGS = 0 V, ID = 250 μA 100 - -	SPECIFICATIONS (T _J = 25 °C	c, unless oth	nerwise noted)				
Drain-Source Breakdown Voltage V _{DS} V _{GS} = 0 V, I _D = 250 μA 100 - - Gate Threshold Voltage V _{GS} (m) V _{DS} = V _{GS} , I _D = 250 μA 2 - 4 Gate-Body Leakage I _{GSS} V _{DS} = 0 V, V _{GS} = 0 V - - ± 100 r Zero Gate Voltage Drain Current I _{DSS} V _{DS} = 100 V, V _{GS} = 0 V - - 1 1 V _{DS} = 100 V, V _{GS} = 0 V, T _J = 55 °C - - - 10 - - - 10 - - - 10 - - - 10 - - - 10 -	PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Gate Threshold Voltage V _{GS(th)} V _{DS} = V _{GS} , I _D = 250 μA 2 - 4	Static						
Gate Threshold Voltage V _{GS} (th) V _{DS} = V _{GS} , I _D = 250 μA 2 - 4 Gate-Body Leakage I _{GSS} V _{DS} = 0 V, V _{QS} = ± 20 V - - ± 100 I Zero Gate Voltage Drain Current I _{DSS} V _{DS} = 100 V, V _{QS} = 0 V - - - 10 I On-State Drain Current a I _{DSON} V _{DS} = 100 V, V _{QS} = 0 V, T _J = 125 °C - - - 2 r On-State Drain Current a I _{DSON} V _{DS} = 10 V, V _{QS} = 0 V, T _J = 125 °C - - - 2 r Drain-Source On-State Resistance a R _{DS(on)} V _{DS} = 10 V, I _D = 30 A - 1.7 2.2 r Envard Transconductance a g _{fs} V _{DS} = 10 V, I _D = 30 A - 65 - - - 65 -	Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	100	-	-	V
	Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2	-	4	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			V _{DS} = 100 V, V _{GS} = 0 V	-	-	1	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$	-	-	10	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			V _{DS} = 80 V, V _{GS} = 0 V, T _J = 125 °C	-	-	2	mA
Forward Transconductance a g_{fs} $V_{DS} = 10 \text{ V}$, $I_{D} = 30 \text{ A}$ - 65 - Dynamic b Input Capacitance C_{fss} $V_{GS} = 0 \text{ V}$, $V_{DS} = 50 \text{ V}$, $f = 1 \text{ MHz}$ - 10800 - Output Capacitance C_{oss} $V_{GS} = 0 \text{ V}$, $V_{DS} = 50 \text{ V}$, $f = 1 \text{ MHz}$ - 1860 - Reverse Transfer Capacitance C_{rss} - 52 - Total Gate Charge c Q_{g} - 166 - Gate-Source Charge c Q_{gs} $V_{DS} = 50 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_{D} = 30 \text{ A}$ - 36 - Gate-Drain Charge c Q_{gd} f = 1 MHz - 1.4 - Gate Resistance Rg f = 1 MHz - 1.4 - Turn-On Delay Time c t _f $V_{DD} = 50 \text{ V}$, $R_{L} = 1.67 \Omega$ - 52 - Turn-Off Delay Time c t _f $I_{D} \cong 30 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_{g} = 1 \Omega$ - 107 - Fall Time c t _f <	On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	280	-	-	Α
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30 A	-	1.7	2.2	mΩ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Forward Transconductance a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	65	-	S
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Dynamic ^b						
Reverse Transfer Capacitance C_{rss} - 52 - Total Gate Charge ° Q_g $V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 30 \text{ A}$ - 166 - Gate-Source Charge ° Q_{gd} $V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 30 \text{ A}$ - 36 - r Gate Resistance R_g $f = 1 \text{ MHz}$ - 1.4 - - 35 - - 43 - - 43 - - 43 - - 43 - - 43 - - 43 - - 43 - - - 43 - - - 43 -	Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 50 V, f = 1 MHz	-	10800	-	pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Capacitance	C _{oss}		-	1860	-	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Reverse Transfer Capacitance	C _{rss}		-	52	-	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Total Gate Charge ^c	Qg		-	166	-	nC
Gate Resistance Rg f = 1 MHz - 1.4 - Turn-On Delay Time $^{\circ}$ $t_{d(on)}$ - 43 - Rise Time $^{\circ}$ t_r $V_{DD} = 50 \text{ V}$, $R_L = 1.67 \Omega$ - - 52 - Turn-Off Delay Time $^{\circ}$ $t_{d(off)}$ $I_D \cong 30 \text{ A}$, $V_{GEN} = 10 \text{ V}$, $R_g = 1 \Omega$ - 107 - Fall Time $^{\circ}$ t_f $I_{DE} \cong 30 \text{ A}$, $I_{CE} \cong 25 ^{\circ}\text{C}$ - - 79 - Drain-Source Body Diode Ratings and Characteristics b ($T_C = 25 ^{\circ}\text{C}$) Pulsed Current (t = 100 μs) I_{SM} - - - 1120 Forward Voltage a V_{SD} $I_F = 30 \text{ A}$, $V_{GS} = 0 \text{ V}$ - - - 1.2 Reverse Recovery Time t_{rr} $I_F = 30 \text{ A}$, $I_{SM} = 100 \text{ A}$ - 5 - Peak Reverse Recovery Charge $I_{RM(REC)}$ $I_F = 30 \text{ A}$, $I_{SM} = 100 \text{ A}$ - 5 -	Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	36	-	
Turn-On Delay Time $^{\circ}$ $t_{d(on)}$ $V_{DD} = 50 \text{ V}$, $R_L = 1.67 \Omega$ $ 43$ $-$ Rise Time $^{\circ}$ t_r $V_{DD} = 50 \text{ V}$, $R_L = 1.67 \Omega$ $ 52$ $-$ Turn-Off Delay Time $^{\circ}$ t_f $ -$	Gate-Drain Charge ^c	Q _{gd}		-	35	-	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	Gate Resistance	Rg	f = 1 MHz	-	1.4	-	Ω
Turn-Off Delay Time $^{\circ}$ $t_{d(off)}$ $I_{D}\cong 30 \text{ A, } V_{GEN} = 10 \text{ V, } R_{g} = 1 \Omega$ $ 107$ $ 79$ $ -$	Turn-On Delay Time ^c	t _{d(on)}		-	43	-	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Rise Time ^c	t _r	V_{DD} = 50 V, R_L = 1.67 Ω	-	52	-	ns
Drain-Source Body Diode Ratings and Characteristics b ($T_C = 25$ °C) Pulsed Current (t = 100 μs) I_{SM} - - 1120 Forward Voltage a V_{SD} $I_F = 30$ A, $V_{GS} = 0$ V - - 1.2 Reverse Recovery Time t_{rr} - 88 - - Peak Reverse Recovery Charge $I_{RM(REC)}$ $I_F = 30$ A, di/dt = 100 A/μs - 5 -	Turn-Off Delay Time ^c	t _{d(off)}		-	107	-	
Pulsed Current (t = 100 μs) I_{SM} - - 1120 Forward Voltage α V_{SD} $I_{F} = 30 \text{ A}, V_{GS} = 0 \text{ V}$ - - 1.2 Reverse Recovery Time t_{rr} - 88 - - Peak Reverse Recovery Charge $I_{RM(REC)}$ $I_{F} = 30 \text{ A}, \text{ di/dt} = 100 \text{ A/μs}$ - 5 -	Fall Time ^c	t _f		-	79	-	
Forward Voltage a V_{SD} $I_{F} = 30 \text{ A}, V_{GS} = 0 \text{ V}$ 1.2 Reverse Recovery Time t_{rr} - 88	Drain-Source Body Diode Ratings ar	nd Characteris	stics ^b (T _C = 25 °C)				
Reverse Recovery Time t_{rr} $-$ 88 $-$ Peak Reverse Recovery Charge $I_{RM(REC)}$ $I_F = 30 \text{ A, di/dt} = 100 \text{ A/µs}$ $-$ 5 $-$	Pulsed Current (t = 100 μs)	I _{SM}		-	-	1120	Α
Peak Reverse Recovery Charge $I_{RM(REC)}$ $I_F = 30 \text{ A, di/dt} = 100 \text{ A/µs}$ - 5 -	Forward Voltage ^a	V _{SD}	I _F = 30 A, V _{GS} = 0 V	-	-	1.2	٧
, 3	Reverse Recovery Time	t _{rr}		-	88	-	ns
	Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 30 A, di/dt = 100 A/μs	-	5	-	Α
	Reverse Recovery Charge			-	300	-	nC

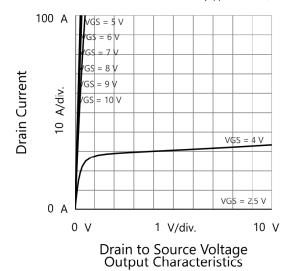
Notes

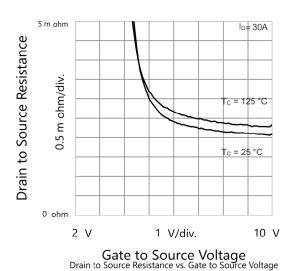
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

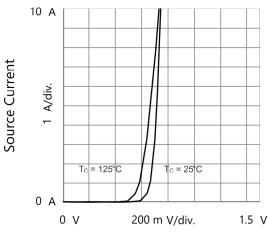
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



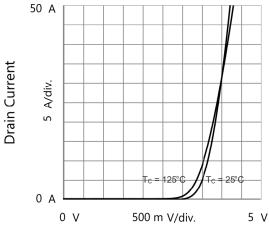
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



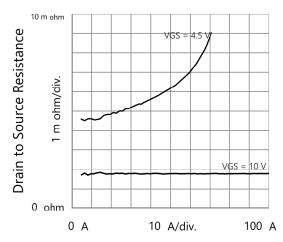




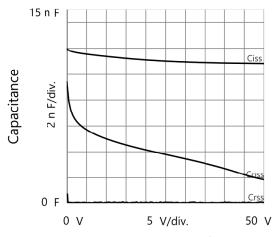
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



Drain Current Drain to Source Resistance vs. Drain Current



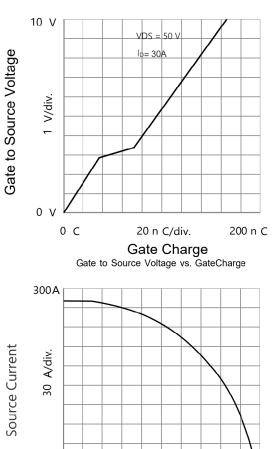
Drain to Source Voltage Capacitances

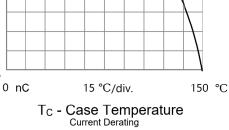


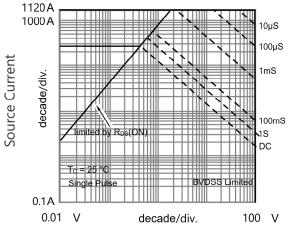
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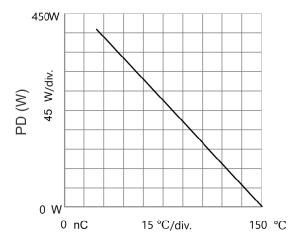
TYPICAL CHARACTERISTICS ($T_A = 25~^{\circ}C$, unless otherwise noted)







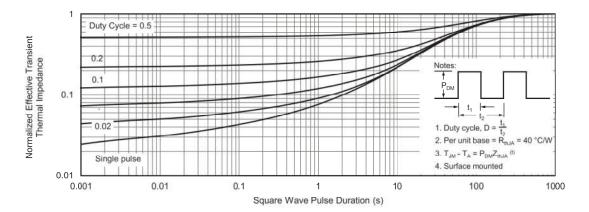
Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature

Power Derating

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient





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